

## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	25	V
Gate-Source Voltage		V <sub>GSS</sub>	8	V
Continuous Drain Current, V <sub>GS</sub> = 4.5V (Note 6)	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	۱ <sub>D</sub>	0.24 0.19	А
Continuous Drain Current, V <sub>GS</sub> = 2.7V (Note 6)	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	۱ <sub>D</sub>	0.22 0.17	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)		I <sub>DM</sub>	1.5	A

# **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D	0.3	W	
	(Note 6)	PD	0.37		
Thermal Resistance, Junction to Ambient	(Note 5)	D	409	°C/W	
	(Note 6)	R <sub>ØJA</sub>	334		
Thermal Resistance, Junction to Case	(Note 6)	Rejc	137		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

#### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

			-				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)			1	1	1		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	25	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V	
Gate-Body Leakage	I <sub>GSS</sub>	_	-	100	nA	V <sub>GS</sub> = 8V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.65	0.85	1.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	5	_	3.8	4	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 0.4A	
	R <sub>DS(ON)</sub>	_	3.1	5	Ω	V <sub>GS</sub> = 2.7V, I <sub>D</sub> = 0.2A	
Forward Transconductance	Y <sub>fs</sub>	_	1	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> =0.4A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.76	1.2	V	$V_{DS} = V_{GS}, I_{D} = 0.25A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	_	27.9	—		$V_{DS}$ = 10V, $V_{GS}$ = 0V, f = 1MHz	
Output Capacitance	Coss	_	6.1	—	pF		
Reverse Transfer Capacitance	Crss	_	2	—			
Total Gate Charge	Qg	_	0.36	—			
Gate-Source Charge	Q <sub>gs</sub>	—	0.06	—	nC	$V_{GS} = 4.5V, V_{DS} = 5V,$ $I_{D} = 0.2A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	0.04	—			
Turn-On Delay Time	t <sub>D(on)</sub>	_	2.9	—		V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 6V	
Turn-On Rise Time	tr	_	1.8	—	nS		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	6.6	—	ns	$I_D = 0.5A, R_G = 50\Omega$	
Turn-Off Fall Time	t <sub>f</sub>	_	2.3	—	1		

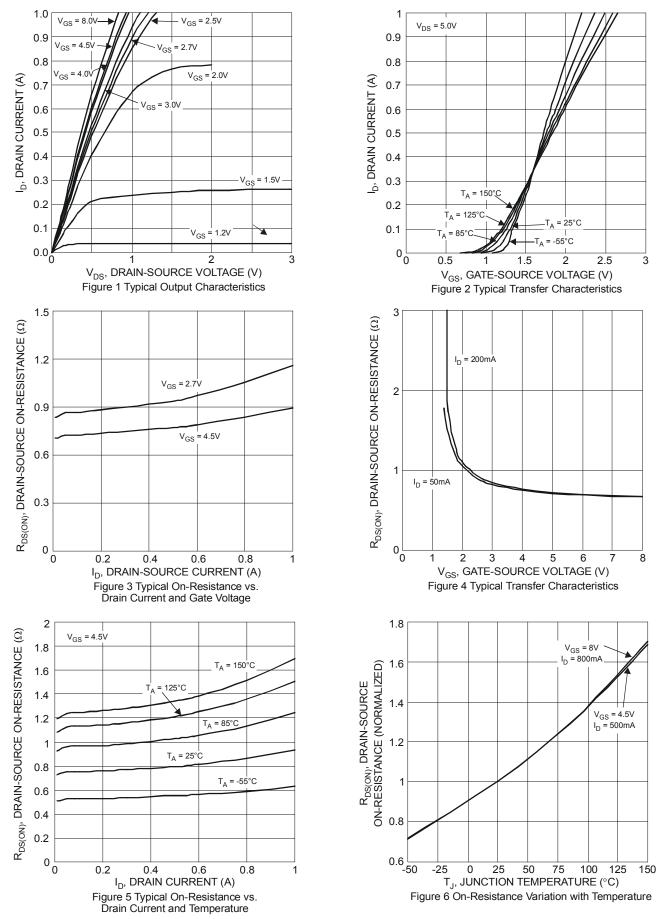
Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout
Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to production testing.

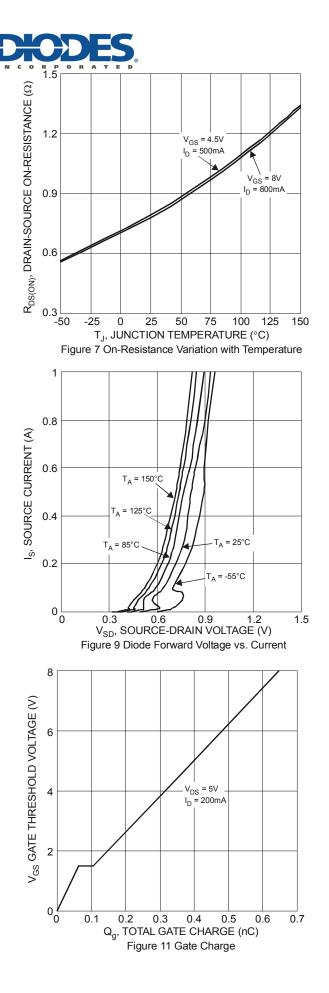


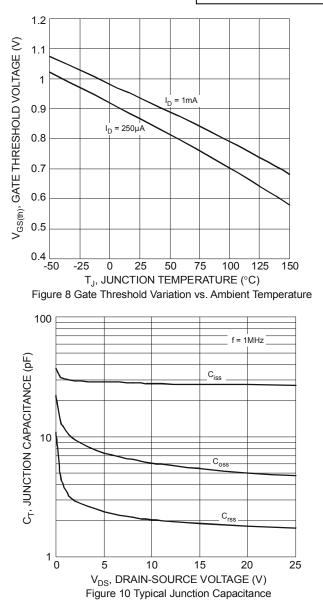
# DMG6301UDW



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# DMG6301UDW

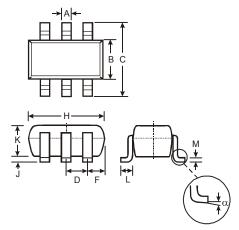






## **Package Outline Dimensions**

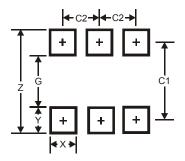
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT363				
Dim	Min	Max		
Α	0.10	0.30		
В	1.15	1.35		
С	2.00	2.20		
D	0.65 Typ			
F	0.40	0.45		
Н	1.80	2.20		
J	0	0.10		
К	0.90	1.00		
L	0.25	0.40		
М	0.10	0.22		
α	0°	8°		
All Dimensions in mm				

## Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Y	0.6
C1	1.9
C2	0.65



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